

# Gul Faroz Ahmad Malik

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5809822/publications.pdf>

Version: 2024-02-01

17  
papers

195  
citations

1307366

7  
h-index

1058333

14  
g-index

17  
all docs

17  
docs citations

17  
times ranked

152  
citing authors

#	ARTICLE	IF	CITATIONS
1	Dilute magnetic semiconductor electrode based all semiconductor magnetic tunnel junction for high-temperature applications. <i>Physica B: Condensed Matter</i> , 2022, 627, 413525.	1.3	5
2	Electric field tunable spin polarization in functionalized silicene. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2022, 429, 127952.	0.9	2
3	Temperature-Dependent High Magnetoresistance in Zigzag Silicene Nanoribbon Heterostructure. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 4010-4015.	1.6	1
4	Silicene/MoS <sub>2</sub> Heterojunction for High-Performance Photodetector. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 138-143.	1.6	20
5	Silicene-Based Spin Filter With High Spin-Polarization. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 5095-5100.	1.6	2
6	First principle study of fluorine functionalized germanene based two probe device. <i>Physica B: Condensed Matter</i> , 2021, 620, 413249.	1.3	1
7	Performance analysis of functionalized silicene nanoribbon based photodetector. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , 2021, 34, .	1.2	6
8	Spin field effect transistors and their applications: A survey. <i>Microelectronics Journal</i> , 2020, 106, 104924.	1.1	15
9	Modelling for triple gate spin FET and design of triple gate spin FET based binary adder. <i>IET Circuits, Devices and Systems</i> , 2020, 14, 464-470.	0.9	6
10	Hydrogenated silicene based magnetic junction with improved tunneling magnetoresistance and spin-filtering efficiency. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2020, 384, 126826.	0.9	13
11	Simulation of Triple Gate Spin Field-Effect Transistor and its Applications to Digital Logic. , 2020, , .		1
12	Electronic Properties of Fluorine Functionalized Germanene Nanoribbons. , 2020, , .		2
13	Performance analysis of indium phosphide channel based sub-10 nm double gate spin field effect transistor. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2020, 384, 126498.	0.9	8
14	Review Silicene: From Material to Device Applications. <i>ECS Journal of Solid State Science and Technology</i> , 2020, 9, 115031.	0.9	65
15	Electrically reconfigurable logic design using multi-gate spin Field Effect Transistors. <i>Microelectronics Journal</i> , 2019, 90, 278-284.	1.1	11
16	Sub-10-nm Silicene Nanoribbon Field Effect Transistor. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 4976-4981.	1.6	37
17	Photo-Detectors Based on Two Dimensional Materials. , 0, , .		0